1. Scope

The present specifications shall apply to an SJPA-L3.

2. Outline

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3. Flammability

UL94V-0(Equivalent)

4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	30	
2	Peak Reverse Voltage	V_{RM}	V	30	
3	Average Forward Current	$I_{F(AV)}$	A	3.0	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	70	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	24.5	1msec≤t≤10msec
6	Junction Temperature	T_j	°C	-40~+125	
7	Storage Temperature	T_{stg}	°C	-40~+125	

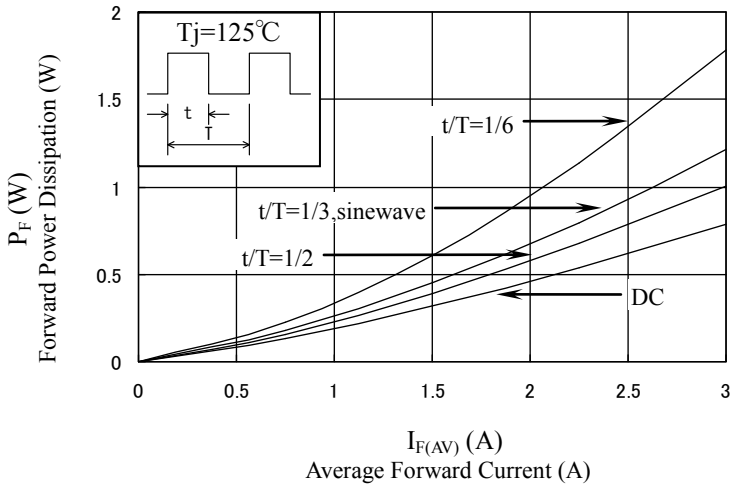
5. Electrical characteristics (Ta=25°C , unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.36 max.	I_F=3.0A
2	Reverse Leakage Current	I_R	mA	4.5 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	210 max.	$V_R=V_{RM}$, T_j=100°C
4	Thermal Resistance	$R_{th(j-l)}$	°C /W	20 max.	Between Junction and Lead

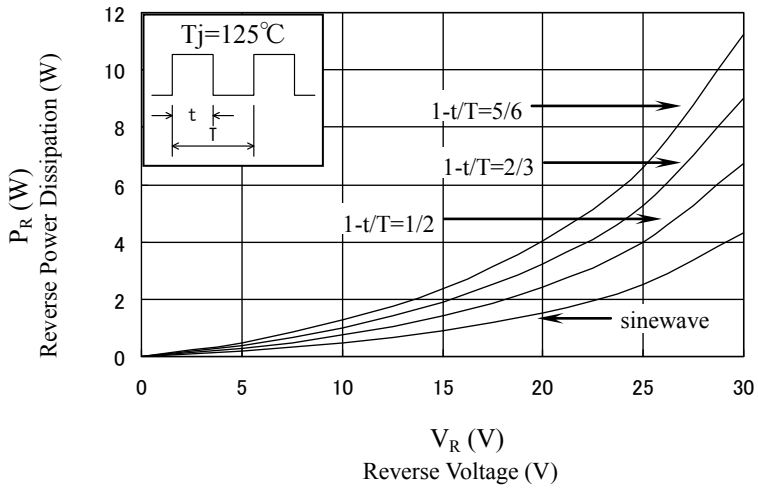
Note) This product is designed in a manner that the forward loss should be minimized, however as a result the reverse leakage current cannot be helped being large.
Therefore, in using product attention should be paid to loss and heat caused by this reverse leakage current.

6. Characteristics

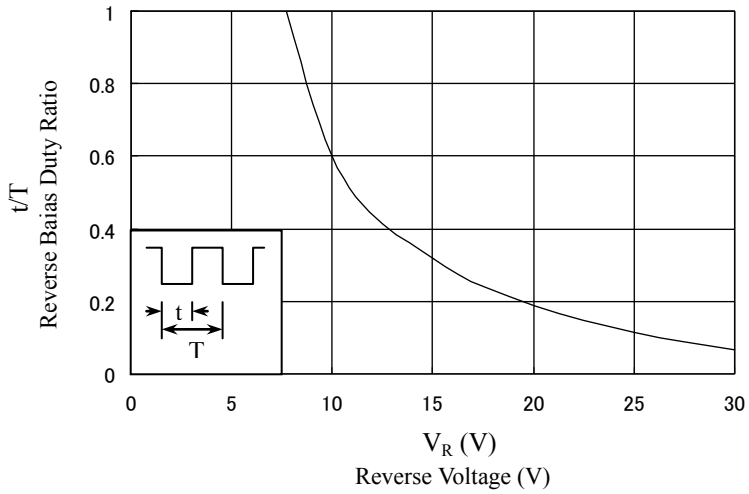
$I_{F(AV)}$ - P_F



V_R - P_R

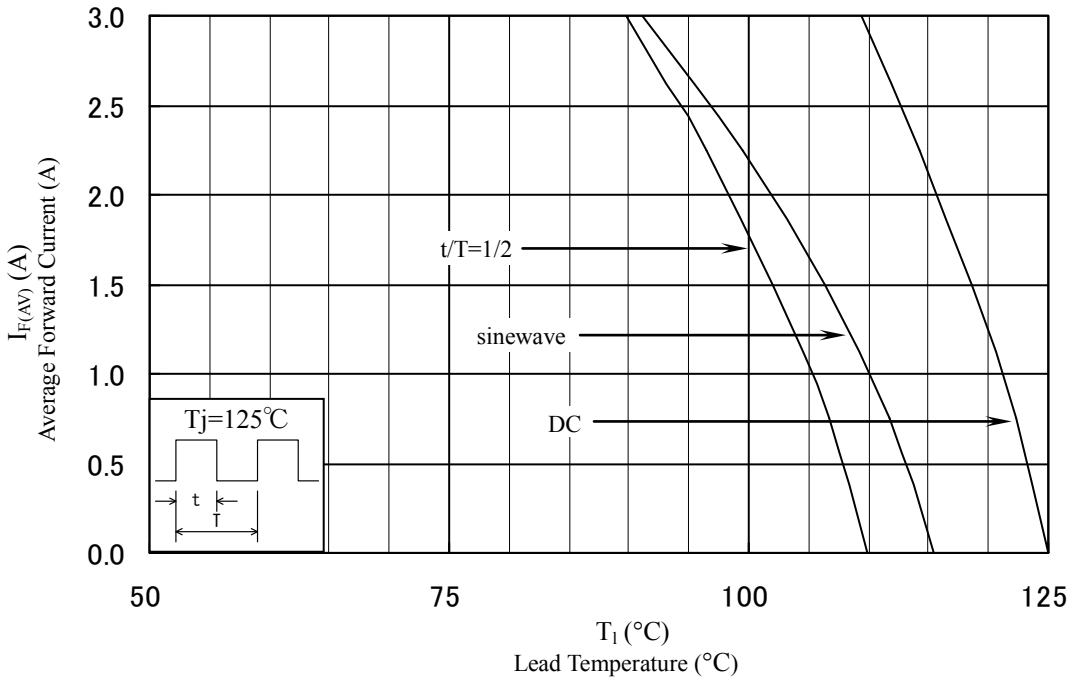


Reverse Voltage Derating

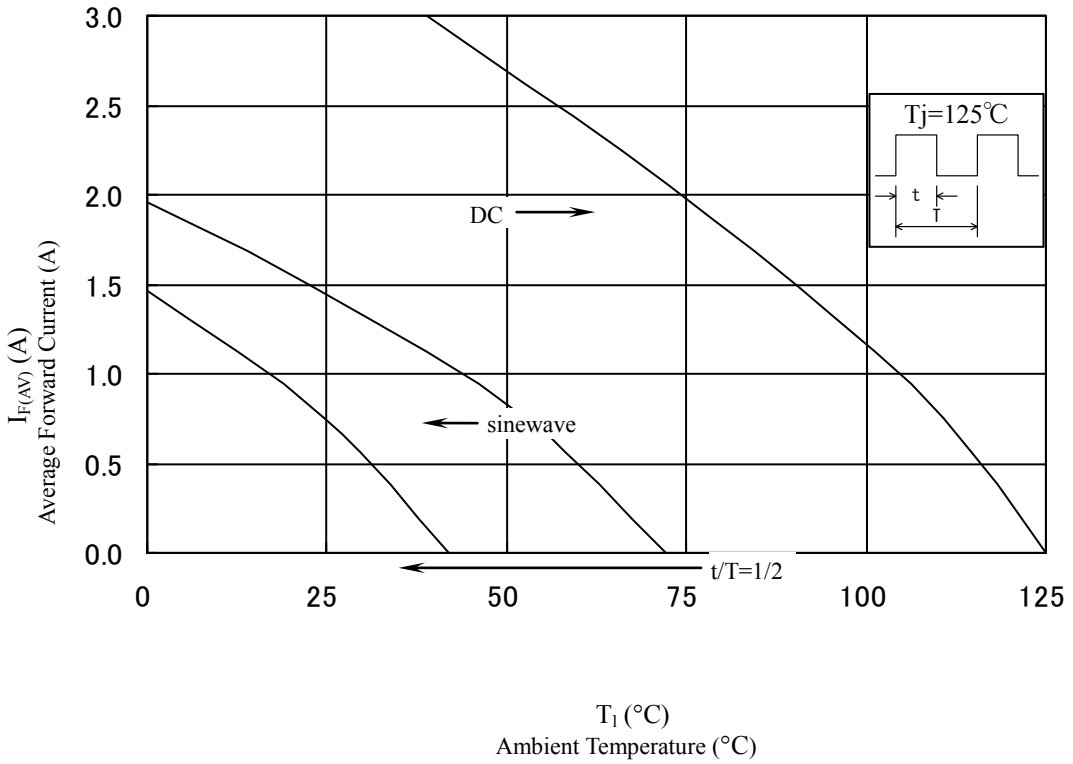


7. Derating

T_l - $I_{F(AV)}$ V_R=10(V)

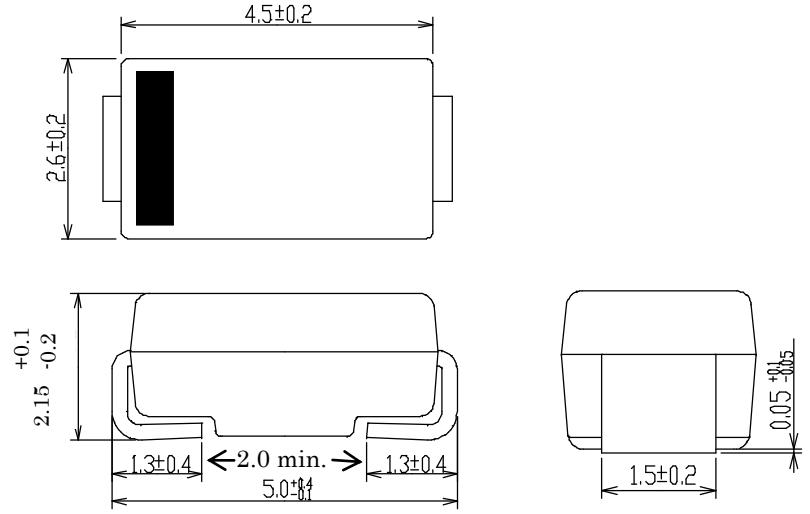


Ta - $I_{F(AV)}$ V_R=10(V)



8. Package information

8-1 Package type, physical dimensions and material

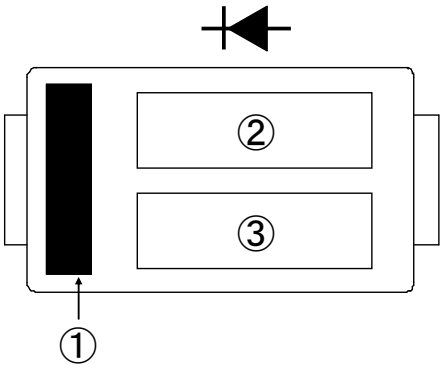


Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



① Polarity marking (Cathode band)

② Type number
SJPA-L3 as abbreviated of AL3

③ Lot number
Example) 6N14
6:Last number of Year
N: Month from 1 to 9 for Jan. to Sep.
O for Oct., N for Nov., D for Dec.
14: Day